ETCHING METHOD, PRECOAT METHOD, AND ETCHING APPARATUS

ABSTRACT

An etching method includes (a) forming a carbon-containing film on a surface of an electrostatic chuck in a chamber, (b) disposing a substrate on the carbon-containing film, and (c) etching the substrate with plasma. (a) includes (a1) supplying a precoat gas containing carbon and hydrogen into the chamber and controlling a pressure in the chamber to be 100 mTorr or more and 1,000 mTorr or less, and (a2) generating the plasma from the precoat gas.

[Fig. 4]